

Amendments to the Abstract

Please replace the abstract of the disclosure with the following new abstract of the disclosure:

In a method for crystallization or dopant
activation heat treatment of a semiconductor film upon
a thermally susceptible non-conducting substrate lying
onto a susceptor, an induction coil is installed in
close proximity of the semiconductor film and disposed
a2 so that the electrical current direction is aligned
parallel to the in-plane direction of the
semiconductor film, and an alternating electrical
current is introduced in the induction coil to
generate an alternating magnetic field through the
semiconductor film heated by the susceptor to the
extent that the semiconductor film can be induction-
heated.
